

NTLGF3402P

Power MOSFET and Schottky Diode

–20 V, –3.9 A FETKY®, P-Channel,
2.0 A Schottky Barrier Diode, DFN6

Features

- Flat Lead 6 Terminal Package 3x3x1 mm
- Enhanced Thermal Characteristics
- Low V_F and Low Leakage Schottky Diode
- Reduced Gate Charge to Improve Switching Response
- This is a Pb-Free Device

Applications

- Buck Converter
- High Side DC-DC Conversion Circuits
- Power Management in Portable, HDD and Computing

MOSFET MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	−20	V
Gate-to-Source Voltage			V_{GS}	±12	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	−2.7	A
		$T_A = 85^{\circ}\text{C}$		−2.0	
		$t \leq 10\text{ s}$		$T_A = 25^{\circ}\text{C}$	
Power Dissipation (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	1.6	W
	$t \leq 10\text{ s}$			3.0	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	−2.3	A
		$T_A = 85^{\circ}\text{C}$		−1.7	
Power Dissipation (Note 2)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	1.14	W
Pulsed Drain Current	$t_p = 10\text{ }\mu\text{s}$		I_{DM}	11	A
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	1.1	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).
2. Surface Mounted on FR4 Board using the minimum recommended pad size (Cu area = 0.5 in sq).



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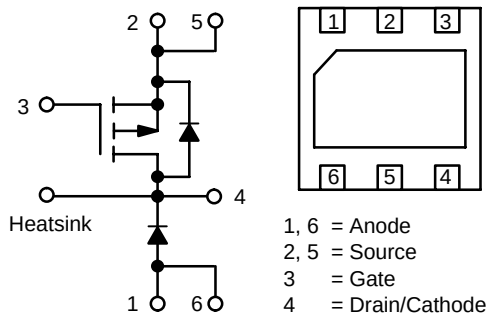
<http://onsemi.com>

MOSFET

$V_{(BR)DS}$	$R_{DS(on)}$ TYP	I_D MAX
–20 V	110 m Ω @ –4.5 V	–3.9 A

SCHOTTKY DIODE

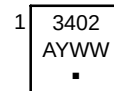
V_R MAX	V_F TYP	I_F MAX
20 V	0.36 V	2.0 A



MARKING DIAGRAMS



DFN6
CASE 506AH



3402 = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
NTLGF3402PT1G	DFN6 (Pb-Free)	3000 / Tape & Reel
NTLGF3402PT2G	DFN6 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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SCHOTTKY DIODE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Max	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	20	V
DC Blocking Voltage	V_R	20	V
Average Rectified Forward Current	I_F	2.0	A

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	110	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 10$ s (Note 2)	$R_{\theta JA}$	58	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	79	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 10$ s (Note 3)	$R_{\theta JA}$	41	$^\circ\text{C/W}$

3. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = -250$ μA	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			-9.0		$\text{mV}/^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -16$ V, $V_{GS} = 0$ V	$T_J = 25^\circ\text{C}$		-1.0	μA
			$T_J = 125^\circ\text{C}$		-5.0	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0$ V, $V_{GS} = \pm 12$ V			± 100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$, $I_D = -250$ μA	-0.6		-2.0	V
Gate Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.7		$\text{mV}/^\circ\text{C}$
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5$ V, $I_D = -2.7$ A		110	140	$\text{m}\Omega$
		$V_{GS} = -2.5$ V, $I_D = -1.0$ A		190	225	
Forward Transconductance	g_{FS}	$V_{DS} = -10$ V, $I_D = -2.7$ A		4.8		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0$ V, $f = 1.0$ MHz, $V_{DS} = -10$ V		230	350	pF
Output Capacitance	C_{OSS}			105	225	
Reverse Transfer Capacitance	C_{RSS}			40	75	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5$ V, $V_{DS} = -10$ V, $I_D = -2.7$ A		3.8	10	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.32		
Gate-to-Source Charge	Q_{GS}			0.7		
Gate-to-Drain Charge	Q_{GD}			1.6		

SWITCHING CHARACTERISTICS (Note 5)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5$ V, $V_{DD} = -16$ V, $I_D = -2.7$ A, $R_G = 2.4$ Ω		6.2	15	ns
Rise Time	t_r			22	30	
Turn-Off Delay Time	$t_{d(OFF)}$			25	45	
Fall Time	t_f			34	60	

4. Pulse Test: Pulse Width ≤ 300 μs , Duty Cycle $\leq 2\%$.

5. Switching characteristics are independent of operating junction temperatures.

NTLGF3402P

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = -1.1\text{ A}$	$T_J = 25^\circ\text{C}$		-0.8	-1.2	V
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, I_S = -1.1\text{ A},$ $dI_S/dt = 100\text{ A}/\mu\text{s}$			53		ns
Charge Time	t_a				15		
Discharge Time	t_b				38		
Reverse Recovery Charge	Q_{RR}				37		nC

SCHOTTKY DIODE ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Instantaneous Forward Voltage	V_F	$I_F = 0.1\text{ A}$		0.32	0.34	V
		$I_F = 1.0\text{ A}$		0.36	0.39	
Maximum Instantaneous Reverse Current	I_R	$V_R = 5\text{ V}, T_J = 100^\circ\text{C}$			12	mA
		$V_R = 10\text{ V}$		70		μA
		$V_R = 20\text{ V}$		225		

6. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$.

7. Switching characteristics are independent of operating junction temperatures.

TYPICAL P-CHANNEL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

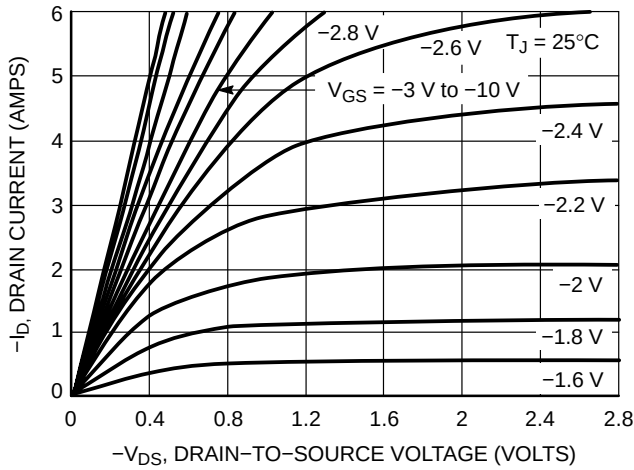


Figure 1. On-Region Characteristics

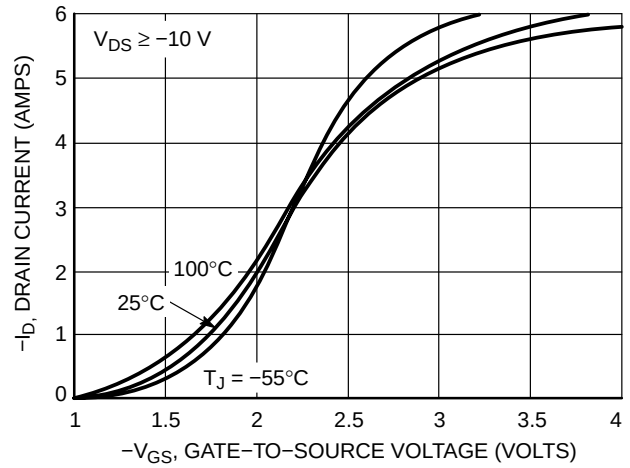


Figure 2. Transfer Characteristics

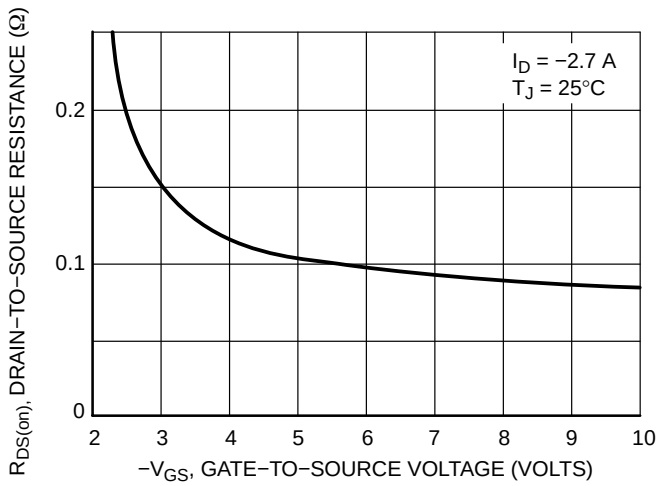


Figure 3. On-Resistance vs. Gate-to-Source Voltage

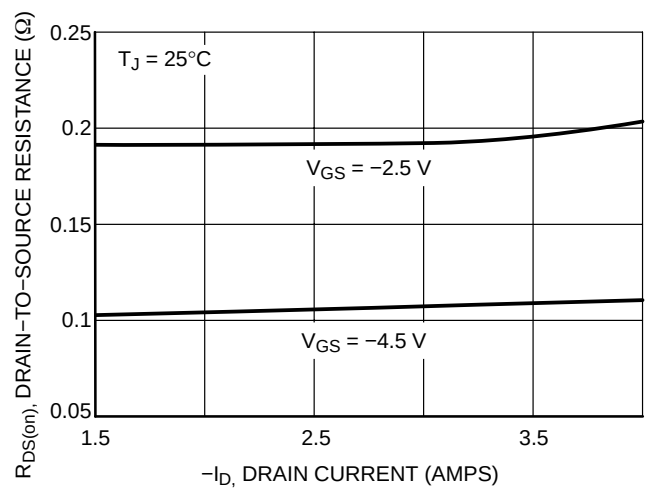


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

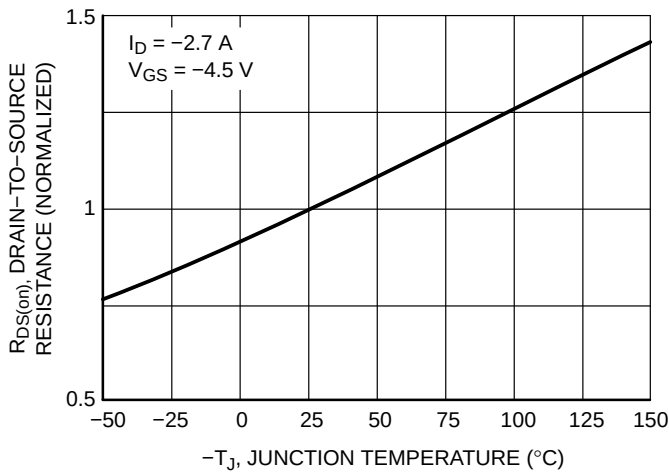


Figure 5. On-Resistance Variation with Temperature

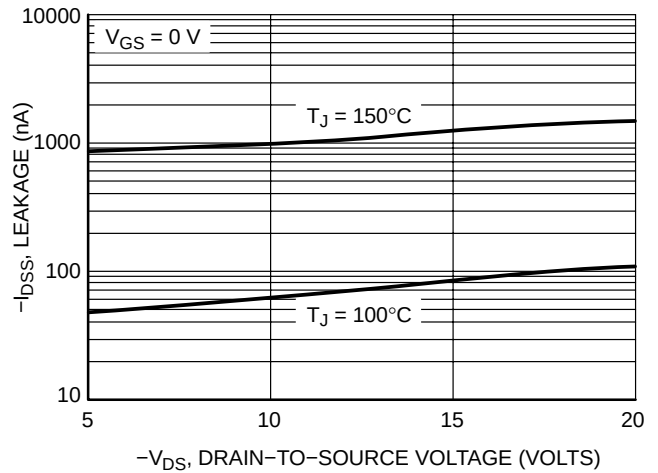
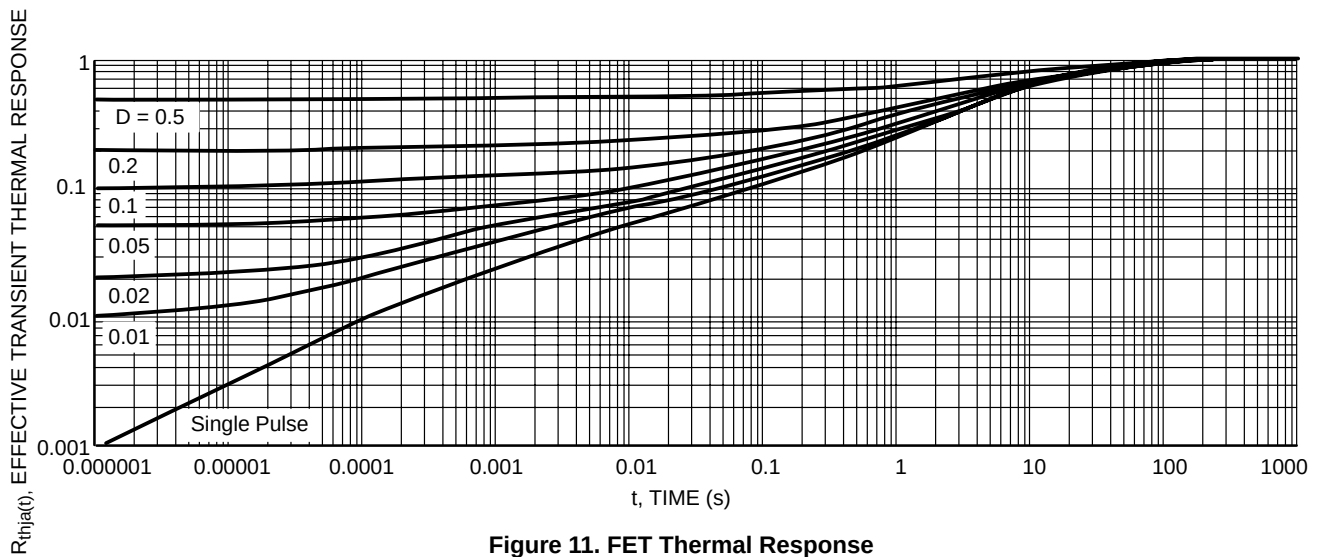
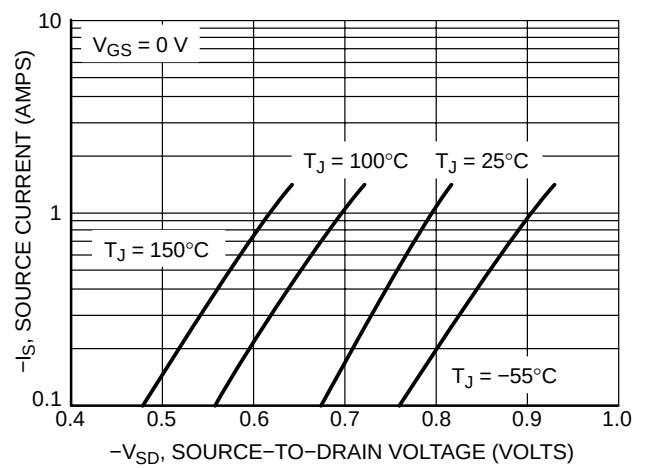
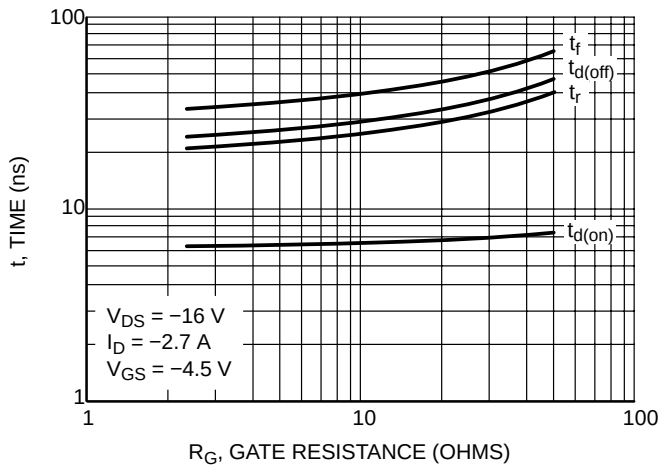
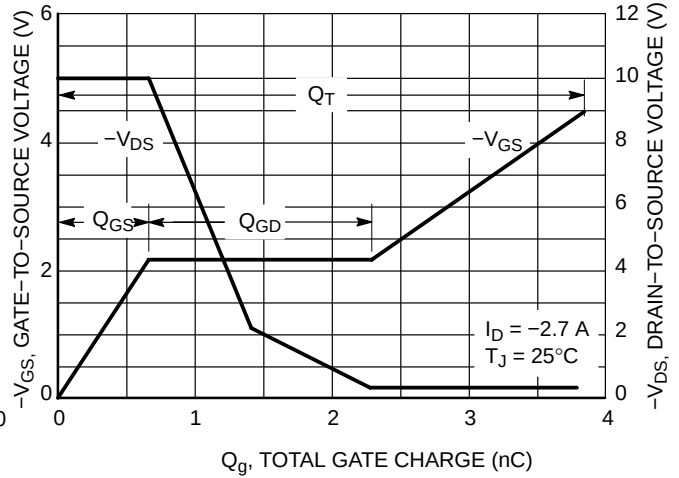
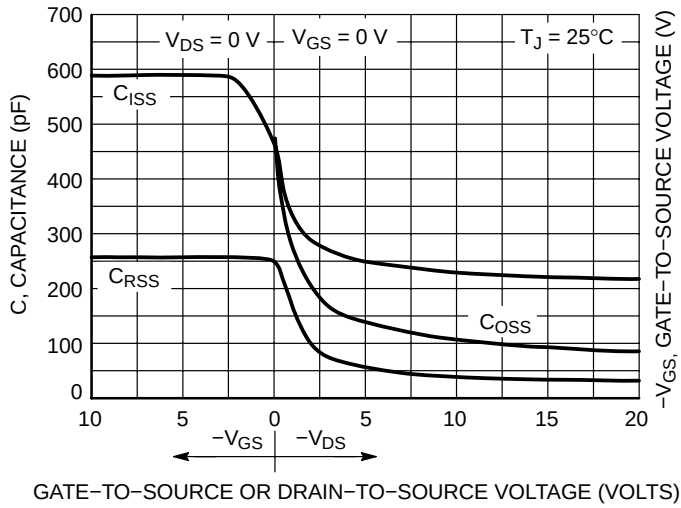


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL P-CHANNEL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)



TYPICAL SCHOTTKY PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

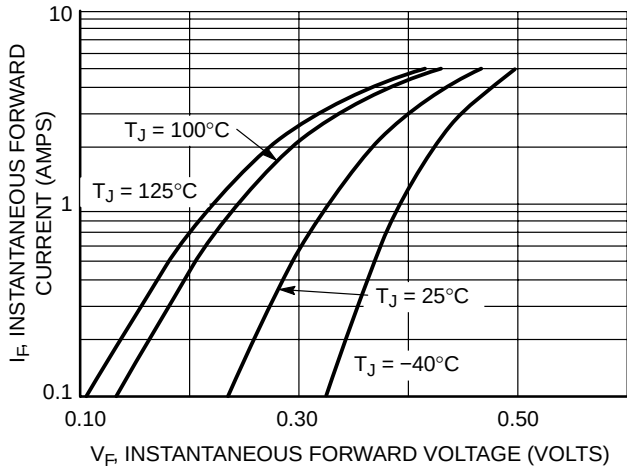


Figure 12. Typical Forward Voltage

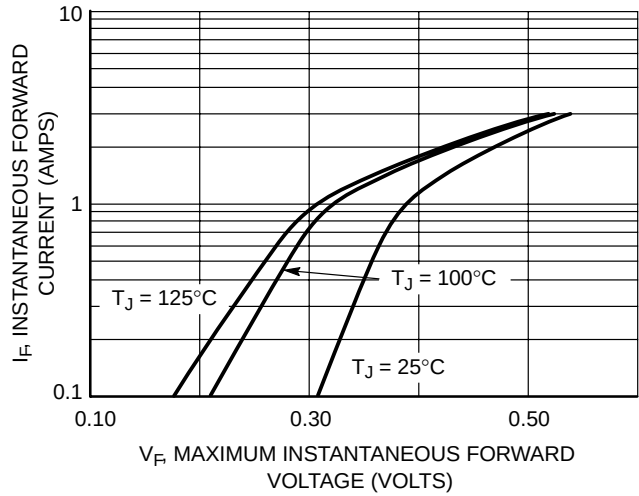


Figure 13. Maximum Forward Voltage

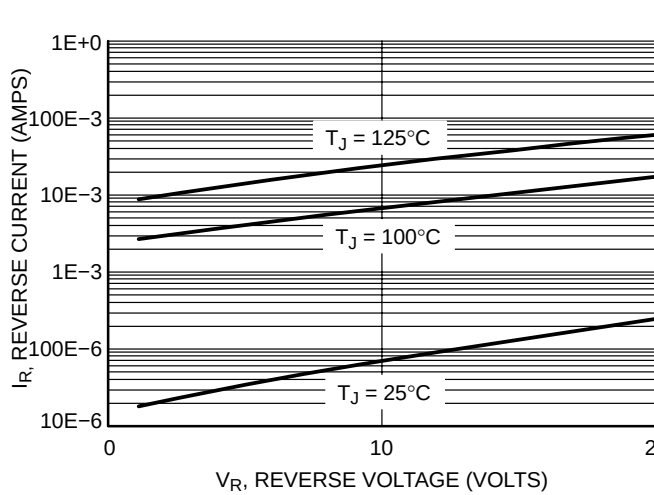


Figure 14. Typical Reverse Current

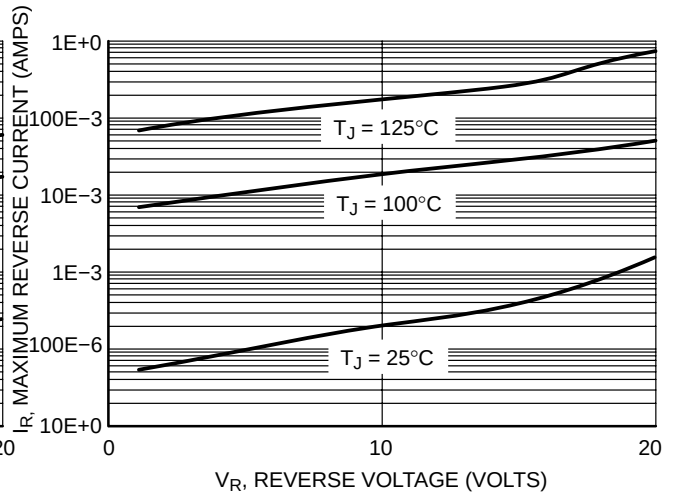


Figure 15. Maximum Reverse Current

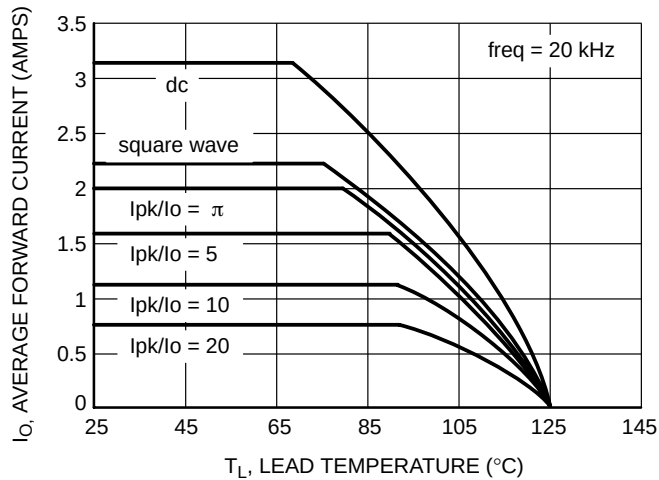


Figure 16. Current Derating

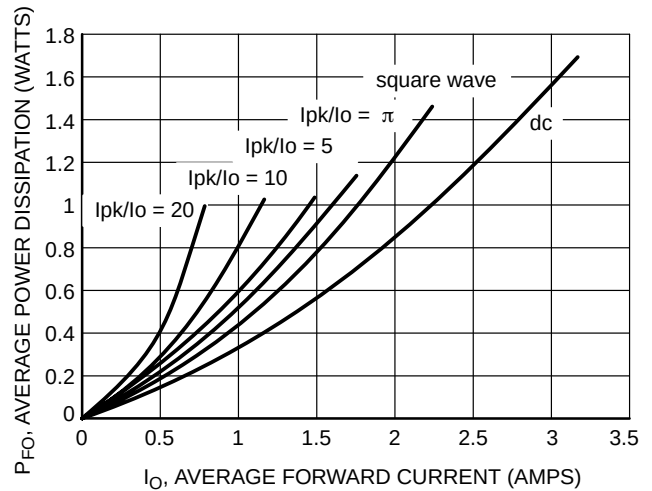
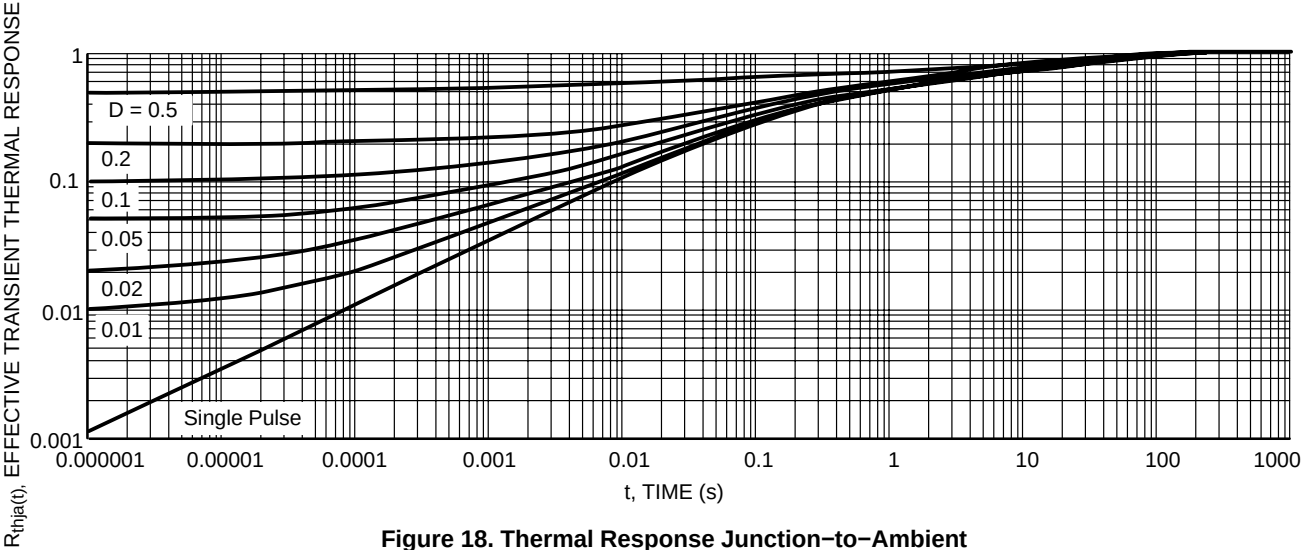


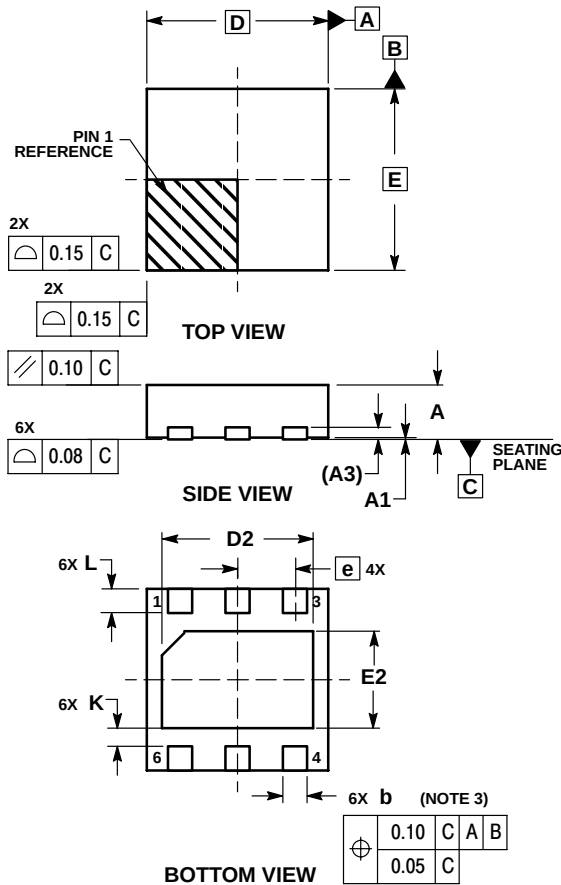
Figure 17. Forward Power Dissipation



NTLGF3402P

PACKAGE DIMENSIONS

DFN6 3*3 MM, 0.95 PITCH
CASE 506AH-01
ISSUE O

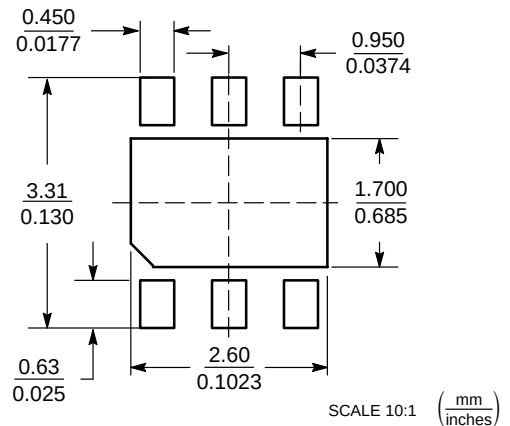


NOTES:

1. DIMENSIONS AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.80	0.90	1.00
A1	0.00	0.03	0.05
A3	0.20 REF		
b	0.35	0.40	0.45
D	3.00 BSC		
D2	2.40	2.50	2.60
E	3.00 BSC		
E2	1.50	1.60	1.70
e	0.95 BSC		
K	0.21	---	---
L	0.30	0.40	0.50

SOLDERING FOOTPRINT*



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NTLGF3402P/D



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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
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- Экспресс доставка в любую точку России;
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- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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